



DATA SHEET

SEMICONDUCTOR

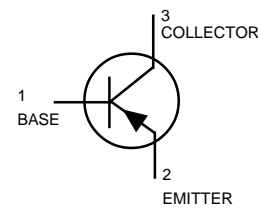
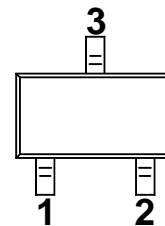
MMBT2907AW

Preliminary Information General Purpose Transistor PNP Silicon



These transistors are designed for general purpose amplifier applications. They are housed in the SOT-323/SC-70 package which is designed for low power surface mount applications.

SOT-323



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CE0}	-60	Vdc
Collector-Base Voltage	V_{CBO}	-60	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current — Continuous	I_C	-600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) $T_A = 25^\circ\text{C}$	P_D	150	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

DEVICE MARKING

MMBT2907AW = 20

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage(2) ($I_C = -10\text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$	-60	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = -10\text{ mAdc}, I_E = 0$)	$V_{(BR)CBO}$	-60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = -10\mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	-5.0	—	Vdc
Base Cutoff Current ($V_{CE} = -30\text{Vdc}, V_{EB(OFF)} = -0.5\text{Vdc}$)	I_{BL}	—	-50	nAdc
Collector Cutoff Current ($V_{CE} = -30\text{Vdc}, V_{EB(OFF)} = -0.5\text{Vdc}$)	I_{CEX}	—	-50	nAdc

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

DEVICE CHARACTERISTICS

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ELECTRICAL CHARACTERISTICS (T A = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain(1) (I _C = -0.1 mA, V _{CE} = -10 Vdc)	h _{FE}	75	—	—
(I _C = -1.0 mA, V _{CE} = -10 Vdc)		100	—	—
(I _C = -10 mA, V _{CE} = -10 Vdc)		100	—	—
(I _C = -150 mA, V _{CE} = -10 Vdc)		100	—	—
(I _C = -500 mA, V _{CE} = -10 Vdc)		50	—	—
Collector-Emitter Saturation Voltage(1) (I _C = -150 mA, I _B = -15 mA)	V _{CE(sat)}	—	-0.4	Vdc
(I _C = -500 mA, I _B = -50 mA)		—	-1.6	
Base-Emitter Saturation Voltage(1) (I _C = -150 mA, I _B = -15 mA)	V _{BE(sat)}	—	-1.3	Vdc
(I _C = -500 mA, I _B = -50 mA)		—	-2.6	

SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product(4) (I _C = -50 mA, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	200	—	MHz
Output Capacitance (V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	—	8.0	pF
Input Capacitance (V _{EB} = -2.0 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	—	30	pF

SWITCHING CHARACTERISTICS

Turn-On Time (V _{CC} = -30 Vdc, I _C = -150 mA, I _{B1} = -15 mA)	t _{on}	—	45	ns
Delay Time	t _d	—	10	ns
Rise Time	t _r	—	40	ns
Storage Time (V _{CC} = -6.0 Vdc, I _C = -150 mA, I _{B1} = I _{B2} = 15 mA)	t _s	—	80	ns
Fall Time	t _f	—	30	ns
Turn-Off Time	t _{off}	—	100	ns

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

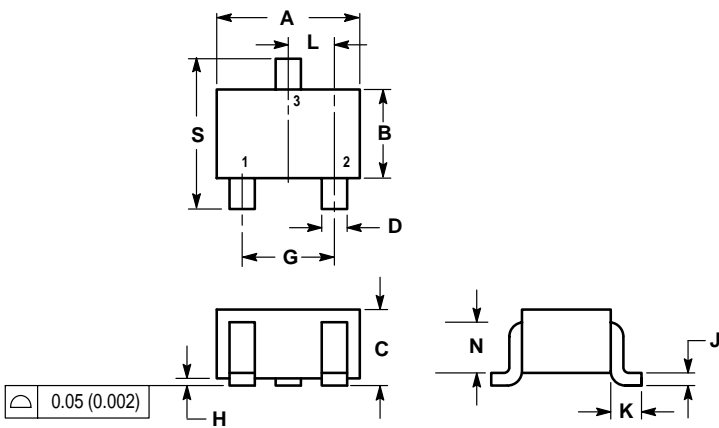
PACKAGE OUTLINE & DIMENSIONS

MMBT2907AW

SC-70 / SOT-323

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017 REF		0.425 REF	
L	0.026 BSC		0.650 BSC	
N	0.028 REF		0.700 REF	
S	0.079	0.095	2.00	2.40

